GeneSiC SEMICONDUCTOR

1N8026-GA

High Temperature Silicon Carbide Power Schottky Diode

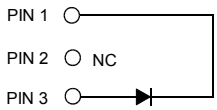
V_{RRM}	=	1200 V
V_F	=	1.6 V
I_F	=	2.5 A
Q_C	=	29 nC

Features

- 1200 V Schottky rectifier
- 250 °C maximum operating temperature
- Electrically isolated base-plate
- Zero reverse recovery charge
- Superior surge current capability
- Positive temperature coefficient of V_F
- Temperature independent switching behavior
- Lowest figure of merit Q_C/I_F
- Available screened to Mil-PRF-19500

Package

- RoHS Compliant



TO – 257 (Isolated Base-plate Hermetic Package)

Advantages

- High temperature operation
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Industry's lowest reverse recovery charge
- Industry's lowest device capacitance
- Ideal for output switching of power supplies
- Best in class reverse leakage current at operating temperature

Applications

- Down Hole Oil Drilling, Geothermal Instrumentation
- High Temperature DC/DC Converters
- High Temperature Motor and Servo Drives
- High Temperature Inverters
- High Temperature Actuator Control
- Military Power Supplies
- Ideal for Aerospace and Defense Applications

Maximum Ratings at T_j = 250 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	I_F	$T_C \le 225$ °C	2.5	A
RMS forward current	$I_{F(RMS)}$	$T_C \le 225$ °C	4.3	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_P = 10 ms	30	A
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25 °C, t_P = 10 µs	tbd	A
I^2t value	$\int i^2\,dt$	T_C = 25 °C, t_P = 10 ms	tbd	A^2S
Power dissipation	P_{tot}	T_C = 25 °C	66	W
Operating and storage temperature	T_j , T_{stg}		-55 to 250	°C

Electrical Characteristics at T_j = 250 °C, unless otherwise specified

Parameter	Symbol	Conditions		Values min.	Values typ.	Values max.	Unit
Diode forward voltage	V_F	I_F = 2.5 A, T_j = 25 °C I_F = 2.5 A, T_j = 210 °C			1.56 2.5		V
Reverse current	I_R	V_R = 1200 V, T_j = 25 °C V_R = 1200 V, T_j = 250 °C			0.9 20.8	10 150	µA
Total capacitive charge	Q_C	$I_F \le I_{F,MAX}$ dI_F/dt = 200 A/µs T_j = 210 °C	V_R = 400 V V_R = 960 V		17 29		nC
Switching time	t_s		V_R = 400 V V_R = 960 V		< 25		ns
Total capacitance	C	V_R = 1 V, f = 1 MHz, T_j = 25 °C V_R = 400 V, f = 1 MHz, T_j = 25 °C V_R = 1000 V, f = 1 MHz, T_j = 25 °C			237 25 20		pF

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	3.4	°C/W

Mechanical Properties

Mounting torque	M	0.6	Nm

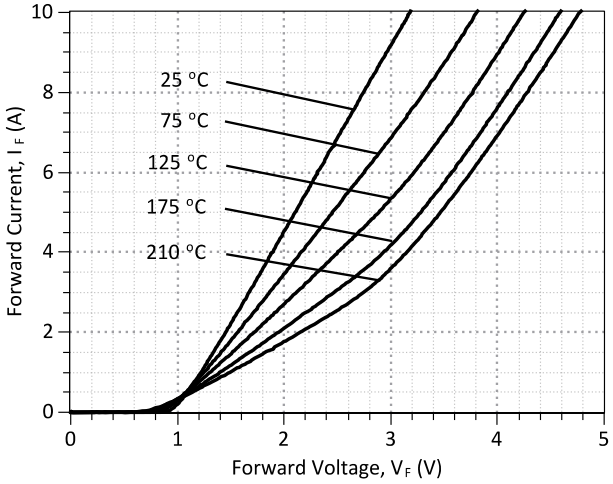


Figure 1: Typical Forward Characteristics

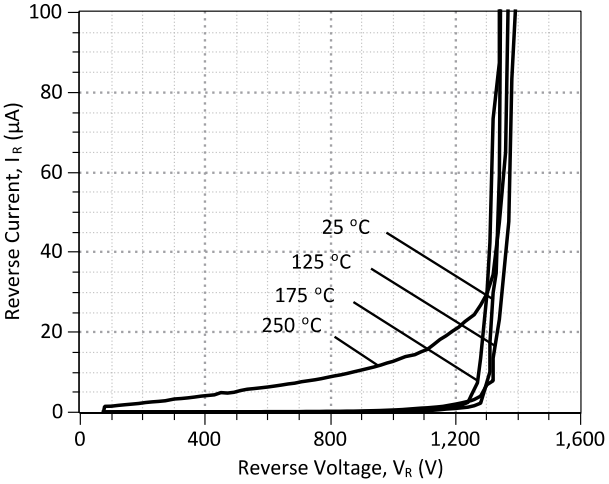


Figure 2: Typical Reverse Characteristics

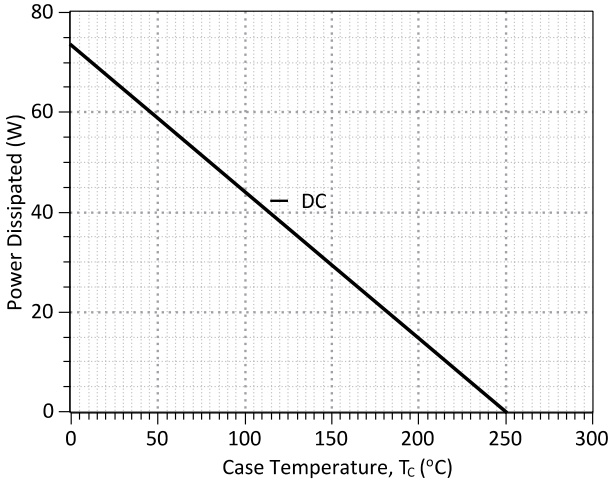


Figure 3: Power Derating Curve

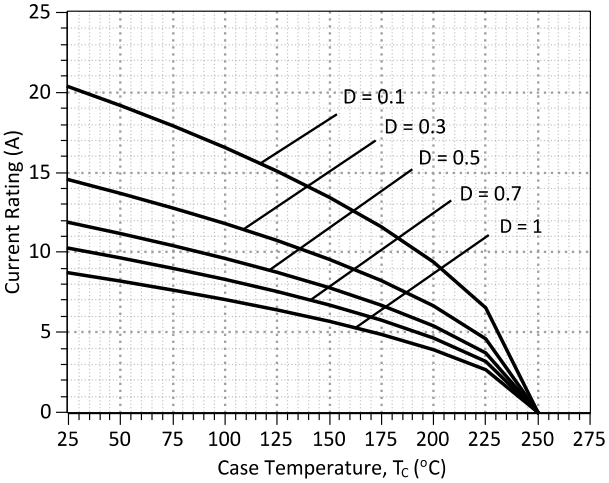


Figure 4: Current Derating Curves (D = t_P/T, t_P= 400 µs) (Considering worst case Z_{th} conditions)

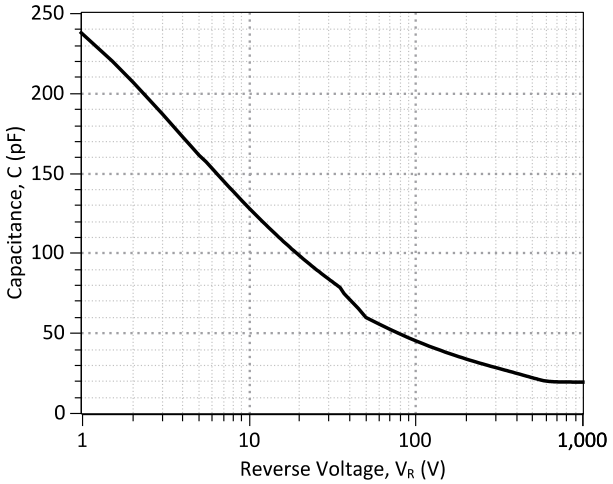


Figure 5: Typical Junction Capacitance vs Reverse Voltage Characteristics

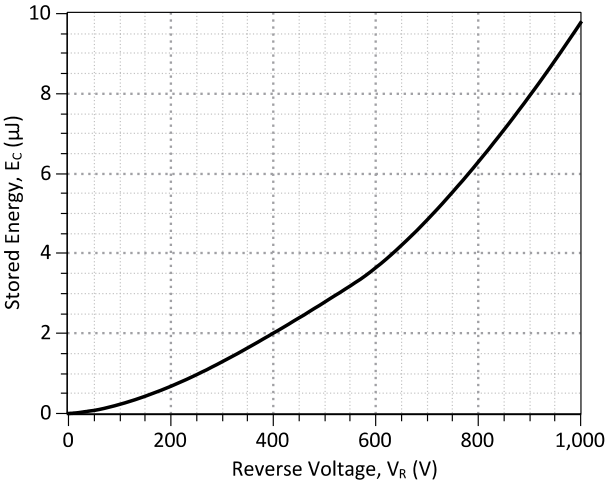


Figure 6: Typical Switching Energy vs Reverse Voltage Characteristics

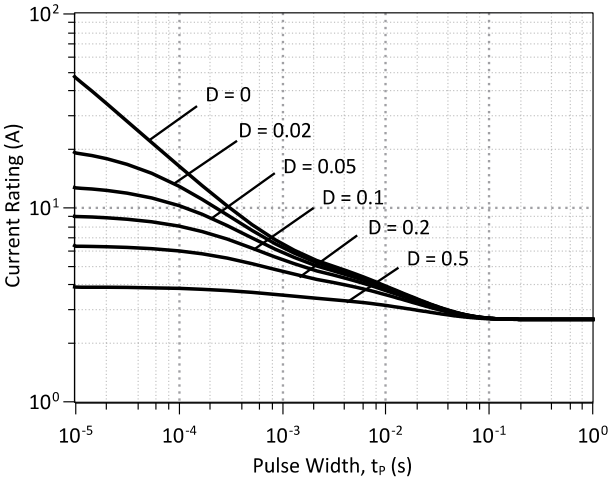


Figure 7: Current vs Pulse Duration Curves at T_C = 225 °C

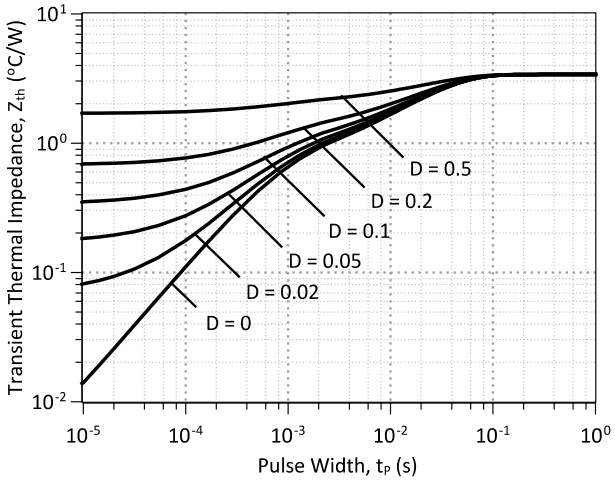
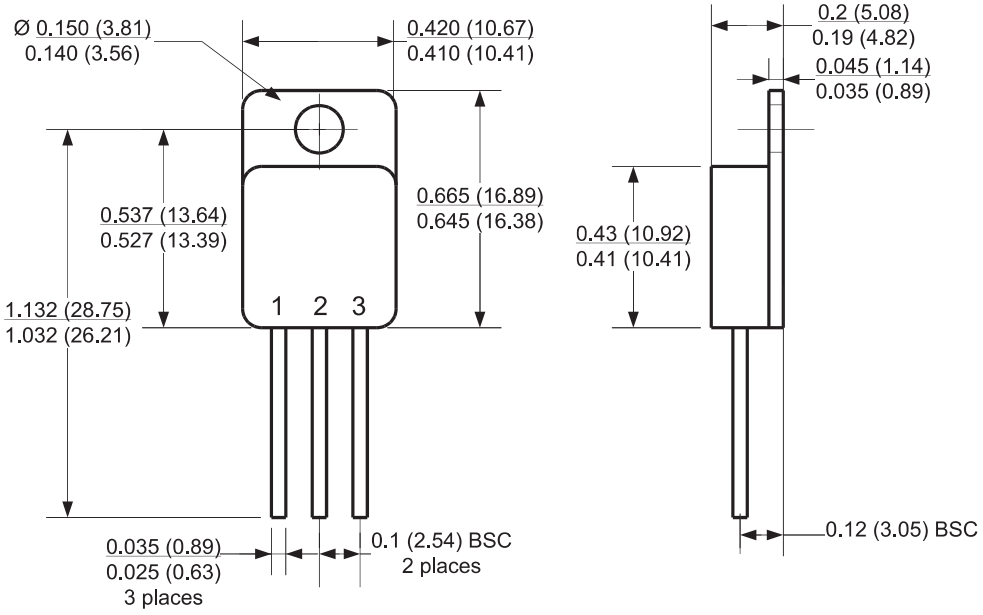


Figure 8: Transient Thermal Impedance

Package Dimensions:

TO-257 **PACKAGE OUTLINE**



NOTE
1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History			
Date	Revision	Comments	Supersedes
2012/04/24	0	Initial release	

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